

Notice of References Cited		Application/Control No. 10/551,843	Applicant(s)/Patent Under Reexamination OHMI ET AL.	
		Examiner Grant S. Withers	Art Unit 2812	Page 1 of 1

U.S. PATENT DOCUMENTS

*	Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A US-2006/0194451	08-2006	Lee et al.	438/786
B	US-			
C	US-			
D	US-			
E	US-			
F	US-			
G	US-			
H	US-			
I	US-			
J	US-			
K	US-			
L	US-			
M	US-			

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O	WO2005/015621	07-2003	PCT	Lim et al.	
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NON-PATENT DOCUMENTS

*	Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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V	International Preliminary Examination Report for PCT/EP 03/50352
W	Gordon, Roy "Vapor Deposition of Metal Oxides and Silicates: Possible Gate Insulators for Future Microelectronics" Chem. Mater. 2001 13 pp 2463-2464
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a))
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.